TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

# 2 S C 5 0 9 5

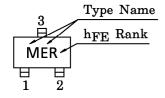
VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

- Low Noise Figure, High Gain.
- NF=1.8dB,  $|S_{21e}|^2 = 7.5dB$  (f=2GHz)

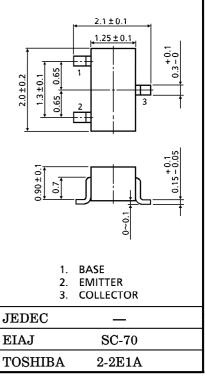
### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{CBO}$	20	V
Collector-Emitter Voltage	$v_{CEO}$	10	V
Emitter-Base Voltage	$V_{ m EBO}$	1.5	V
Base Current	$I_{\mathbf{B}}$	7	mA
Collector Current	$I_{\mathbf{C}}$	15	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	100	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

#### **MARKING**



# Unit in mm



Weight: 0.006g

#### MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	$ m f_T$	$V_{CE}=6V, I_{C}=7mA$	7	10	_	GHz
Insertion Gain	$ S_{21e} ^2$ (1)	$V_{CE}=6V$ , $I_{C}=7mA$ , $f=1GHz$	_	13	_	dB
	$ S_{21e} ^2$ (2)	$V_{CE}=6V$ , $I_{C}=7mA$ , $f=2GHz$	4.5	7.5	_	ub
Noise Figure	NF (1)	$V_{CE}=6V$ , $I_{C}=3mA$ , $f=1GHz$	_	1.4	_	dB
	NF (2)	$V_{CE}=6V$ , $I_{C}=3mA$ , $f=2GHz$	_	1.8	3.0	ub

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 10V, I_E = 0$	_	_	1	$\mu$ A
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=1V, I_{C}=0$	_	_	1	$\mu$ A
DC Current Gain	hFE (Note 1)	$V_{CE}=6V, I_{C}=7mA$	50	_	160	_
Output Capacitance	$C_{\mathbf{ob}}$	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	0.5	_	pF
Reverse Transfer Capacitance	$\mathrm{C_{re}}$	(Note 2)	_	0.4	0.85	pF

(Note 1) hFE Classification  $R:50\sim100$ ,  $O:80\sim160$ 

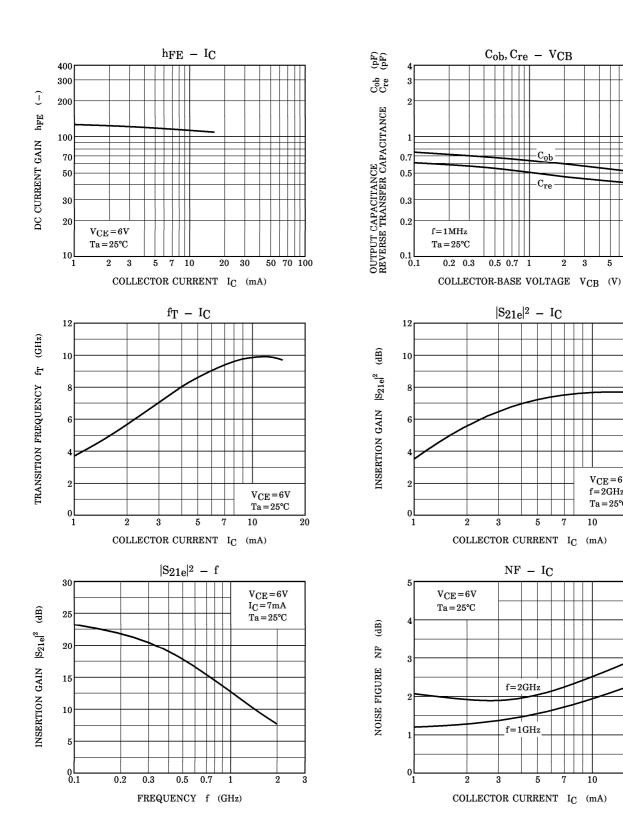
(Note 2) Cre is measured by 3 terminal method with capacitance bridge.

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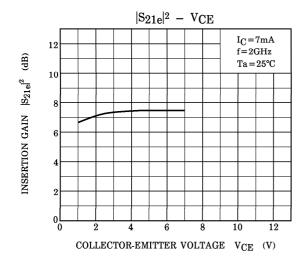
 $V_{CE} = 6V$ f=2GHz

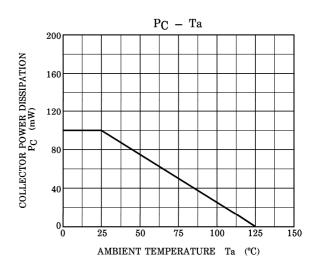
 $\mathrm{Ta} = 25^{\circ}\mathrm{C}$ 

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S-Parameter  $Z_O = 50\Omega$ ,  $Ta = 25^{\circ}C$   $V_{CE} = 6V$ ,  $I_C = 3mA$ 

frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.835	-26.1	7.069	150.4	0.046	71.0	0.899	-19.3
400	0.665	-46.5	5.948	130.4	0.076	60.5	0.745	-30.3
600	0.501	-62.7	5.021	115.2	0.095	55.7	0.630	-35.9
800	0.386	-74.3	4.173	104.3	0.111	53.7	0.552	-38.5
1000	0.297	-83.7	3.592	95.6	0.124	53.2	0.500	-39.9
1200	0.226	-92.7	3.140	88.5	0.137	53.6	0.465	-41.1
1400	0.175	-101.9	2.808	82.3	0.152	54.1	0.442	-42.2
1600	0.130	-113.4	2.514	76.6	0.165	54.2	0.421	-43.8
1800	0.103	-128.0	2.293	71.7	0.179	53.9	0.405	-45.7
2000	0.081	-147.4	2.114	67.3	0.193	54.8	0.388	-47.4

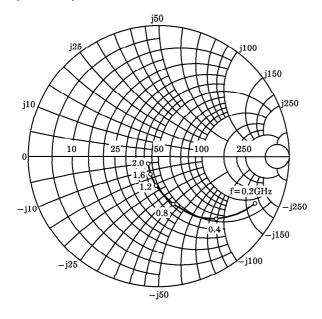
# $V_{CE} = 6V$ , $I_C = 7mA$

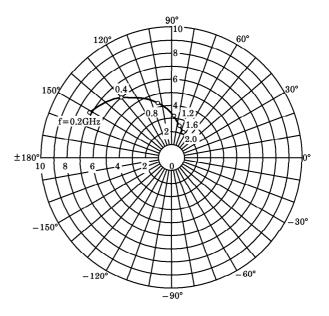
frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.668	-40.0	12.306	138.9	0.040	67.3	0.786	-27.0
400	0.427	-64.4	8.852	116.1	0.061	61.6	0.579	-35.0
600	0.280	-79.5	6.591	102.9	0.078	61.8	0.476	-35.9
800	0.193	-89.7	5.191	94.3	0.096	62.5	0.420	-35.0
1000	0.134	-99.3	4.288	87.8	0.112	63.2	0.390	-34.2
1200	0.088	-112.3	3.661	81.9	0.130	63.8	0.374	-34.0
1400	0.056	-129.8	3.232	76.9	0.150	63.4	0.366	-34.8
1600	0.035	-169.0	2.857	72.1	0.168	62.5	0.356	-36.6
1800	0.040	157.0	2.574	68.1	0.185	61.4	0.347	-39.0
2000	0.054	131.5	2.363	64.3	0.203	61.3	0.338	-40.2

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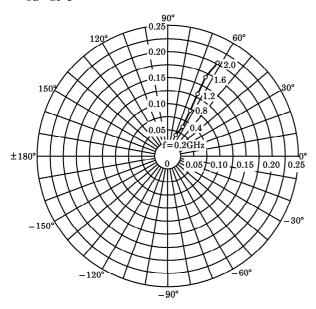
 $\begin{array}{l} S_{11e} \\ V_{CE} \!=\! 6V \\ I_{C} \!=\! 3mA \\ T_{a} \!=\! 25^{\circ}\! C \\ (UNIT:\Omega) \end{array}$ 

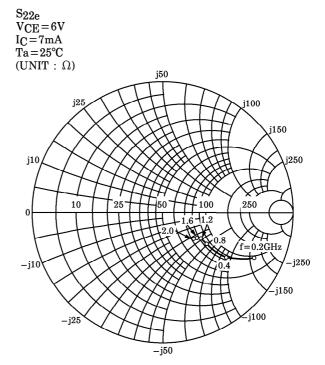






 $S_{12e}$   $V_{CE}=6V$   $I_{C}=7mA$   $Ta=25^{\circ}C$ 

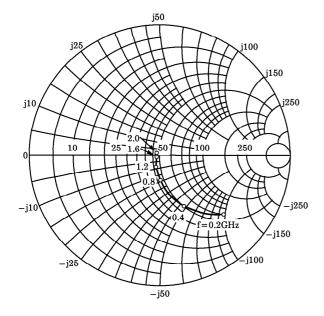


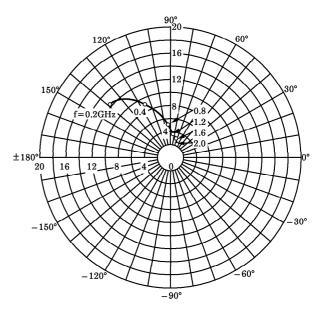


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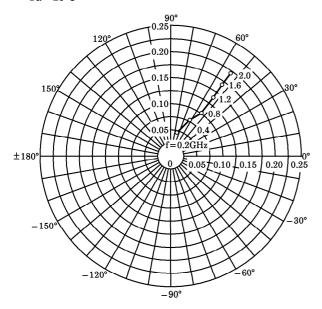
 $\begin{array}{l} S_{11e} \\ V_{CE} = 6V \\ I_{C} = 7mA \\ Ta = 25^{\circ}C \\ (UNIT:\Omega) \end{array}$ 

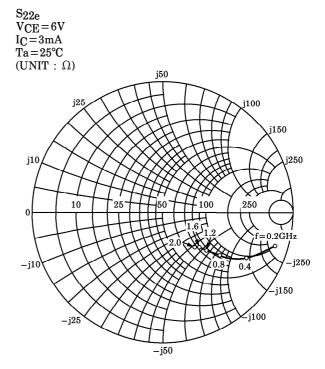






 $\begin{array}{c} S_{12e} \\ V_{CE} = 6V \\ I_{C} = 3mA \\ Ta = 25^{\circ}C \end{array}$ 





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